Introduction

Over the last few decades, there has been an exponential growth in the semiconductor sector spawning new products and technologies. This trend has been recently stimulated by a driving force towards miniaturization, resulting in more compact applications and products being introduced into the industrial, consumer and communications markets. Integrated Circuits have been at the center of this transition, with optocouplers being of no exception.

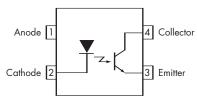


FODB100

MICROCOUPLER™ Package

Description

The FODB100 single channel MICRO-COUPLER is an all Pb-free, low profile miniature surface mount optocoupler in a Ball Grid Array (BGA) package. It consists of an aluminum gallium arsenide infrared emitting diode driving a silicon phototransistor.



FODB100 Schematic

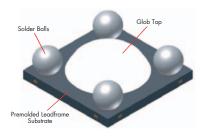
Features

- Low profile package (1.20mm maximum mounted height)
- Land pattern allows for optimum board space savings
- High Current Transfer Ratio (CTR) at low IF
- Minimum isolation distance of 0.45mm
- High steady state isolation voltage of $2500V_{rms}$
- Data rates up to 120Kbits/s (NRZ)
- Minimum creepage distance of 2mm
- Wide operating temperature range of -40 $^{\circ}$ C to +125 $^{\circ}$ C
- Available in tape and reel quantities of 3000 units
- Applicable to Pb-free infrared ray reflow (260°C max)
- UL, VDE certifications pending.

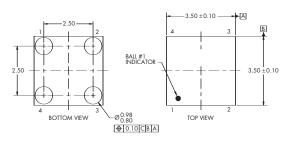
Advantages

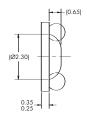
- Improved CTR performance over temperature
- Wide operating temperature range as compared to conventional optocouplers
- Owing to its low profile, small volume and footprint, this package can further save on board real estate giving hardware designers more flexibility and allowing for overall systems cost savings
- High IR reflow soldering capability in lead free environments.

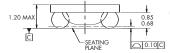
Package Information



Package Dimensions



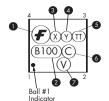




NOTES: UNLESS OTHERWISE SPECIFIED

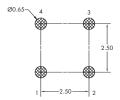
A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) NO JEDEC REGISTRATION REFERENCE AS
OF NOVEMBER 2002.

Marking Information

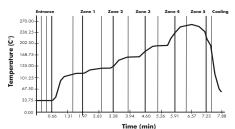


De	finitions
1	Fairchild logo
2	Device number (FODB100)
3	One digit year code e.g. "4" for 2004
4	6-week date code character
5	Die run code
6	Assembly package code
7	VDE 0884 approved (optional)

Recommended Land Pattern



Recommended Infrared Reflow Soldering Profile



Reflow Profile for Pb Free

	Convection Reflow
Average ramp-up rate (183°C to peak)	3°C/sec max
Preheat Temperature 125(±25)°C to 200°C	60-180°C
Temperature maintained above 220°C	60-150 sec
Time within 5°C of actual peak temperature	20-40 sec
Peak temperature range	260 ±5°C
Ramp down rate	6°C/sec max
Time 25°C to peak temperature	8 min max

Note: Surface Mount Adhesives (SMA) isn't recommended to be used on the dome area (white dome).

Notes: 1. All dimensions in mm 2. It is recommended to use 6 mils of stencil thickness on PCB

Electrical Specifications

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)							
Symbol	Value	Units					
T _{STG}	-55 to +150	°C					
T _{OPR}	-40 to +125	°C					
Ti	130	°C					
I _{F (avg)}	30	mA					
V _R	6	٧					
P	40	mW					
, p	0.6	mW/°C					
	50	mA					
P	150	mW					
	1.42	mW/°C					
V _{CEO}	75	٧					
V _{ECO}	7	٧					
	Symbol T STG T OPR T i IF (avg) VR P D P D VCEO	Symbol Value T _{STG} -55 to +150 T _{OPR} -40 to +125 T _i 130 I _F (evg) 30 V _R 6 P _D 40 0.6 50 P _D 150 1.42 VCEO 75					

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$										
INDIVIDUAL COMPONENT CHARACTERISTICS										
Parameters	Parameters Test Conditions Symbol Min Typ Max Unit									
Emitter Forward Voltage	(I _F = 2mA)	V _F	1.0		1.5	٧				
Reverse Current	(V _R = 6V)	I _R			10	μА				
Detector Breakdown Voltage Collector to Emitter	(I _C = 100mA, I _F = 0)	BV _{CEO}	75			٧				
Emitter to Collector	$(I_E = 100\mu A, F = 0)$	BV _{ECO}	7							
Collector Dark Current	$(V_{CE} = 75V, I_F = 0)$	I _{CEO}			100	nA				
Capacitance	$(V_{CE} = 0V, f = 1MHz)$	C _{CE}		8		pF				

Electrical Specifications

Characteristic	Test Conditions	Symbol	Min	Тур	Max	Unit	
Current Transfer Ratio ¹	$(I_F = 1 \text{ mA}, V_{CE} = 5V)$	CTR	100			%	
Saturated Current Transfer	$(I_F = 1.6 \text{mA}, V_{CE} = 0.4 \text{V})$	CTP	100			%	
Ratio (Collector to Emitter)	$(I_F = 1.0 \text{mA}, V_{CE} = 0.4 \text{V})$	CTR _{CE(SAT)}	75			/0	
Saturation Voltage	$(I_F = 3.0 \text{mA}, I_C = 1.8 \text{mA})$ $(I_F = 1.6 \text{mA}, I_C = 1.6 \text{mA})$	V _{CE(SAT)}			0.4	٧	
Rise Time (Non-Saturated)	$(I_C = 2mA, V_{CE} = 5V)$ $(R_L = 1K)$	t _r		1		116	
Fall Time (Non-Saturated)	$(I_C = 2mA, V_{CE} = 5V)$ $(R_L = 1K)$			5		μs	
Propagation Delay	$I_F = 1.6 \text{mA}, V_{CC} = 5.0 \text{V}$ $R_L = 750$. T _{PHI} .		3		μѕ	
High to Low	$I_F = 1.6 \text{mA}, V_{CC} = 5.0 \text{V}$ $R_L = 4.7 \text{K}$, LHT		12		μς	
Propagation Delay	$I_F = 1.6 \text{mA}, V_{CC} = 5.0 \text{V}$ $R_L = 750$	T _{PLH}		5		116	
Low to High	$I_F = 1.6 \text{mA}, V_{CC} = 5.0 \text{V}$ $R_L = 4.7 \text{K}$	PLH		19		μs	

ISOLATION CHARACTERISTICS								
Characteristic Test Conditions Symbol Min Typ Max Unit								
Steady State Isolation Voltage ²	(RH ≤ 50%, T _A = 25°C, t = 1 sec)	V _{ISO}	2500			V(rms)		
Resistance (input to output) ²	(V _{I-O} = 500 VDC)	R ISO	10 ¹²					
Capacitance (input to output) ²	f = 1MHz	C _{ISO}		0.3	0.5	pF		

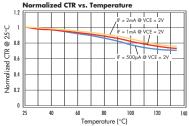
Notes:

1. CTR bin (FODB100 only) FODB101: 100% – 200% FODB102: 150% – 300%

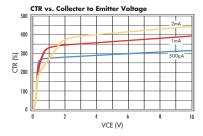
2. Pin 1 and Pin 2 are shorted as input and Pin 3 and Pin 4 are shorted as output.

Typical Characteristic Curves

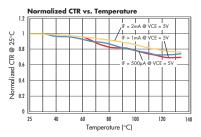
Normalized CTR at Vce = 2V



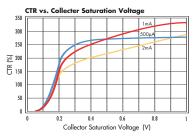
CTR vs. Vce



Normalized CTR at $V_{ce} = 5V$



CTR vs. Vce(SAT)



Applications, Markets, Safety Approvals

Primary Application:

Feedback loop switch mode power supply

Secondary Application:

Ground loop isolation and signal to noise isolation

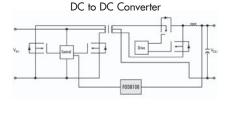
Target Markets:

- Communications chargers, adapters
- Consumer appliances, set top boxes
- Industrial power supplies, motor control

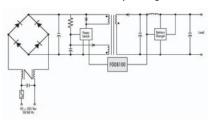
Safety Agency Approvals:

UL and VDE certifications pending

Application Schematic Diagrams:

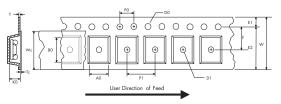


AC to DC Battery Charger



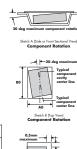
Tape and Reel Specifications

Optocoupler Embossed Carrier Tape Configuration



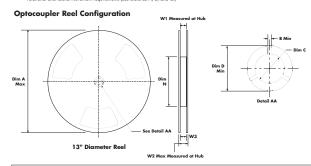
	Dimensions are in millimeters													
Pkg Type	A0 B0 W D0 D1 E1 E2 F P1 P0 K0 T Wc									Tc				
Optocoupler (12mm)	3.80 ±0.10	3.80 ±0.10	12.0 +0.3/ -0.1	1.50 +0.25/ - 0.00	1.50 +0.25/ - 0.00	1.75 ±0.10	10.25 min	5.50 ±0.05	8.0 ±0.1	4.0 ±0.1	1.40 ±0.10	0.279 ±0.02	0.2 ±0.3	0.06 ±0.02

Note: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C.)





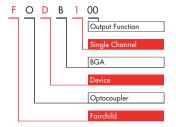
onent lateral move



	Dimensions are in inches and millimeters									
Tape Size	Tape Size Reel Option Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W3 (LSL-I									
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/-0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	

Ordering Information

FODB100



Roadmap

April 2004	June 2004	July 2004	Q4 2004
Introduce single channel, transistor output: FODB100	Introduce 5300V Viso version of FODB100 series	Introduce quad channel, transistor output: FODBQ4XX	Introduce various output functions with single and multiple channels

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